# Yue Kuo

List of Publications by Year
in descending order

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| 226 | 2,129 | 218677 | 330143 |
|---|---|---|---|
| papers | citations | 26 h-index | 37 g-index |

| 230 | 230 | 230 | 994 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Facing the headaches of early failures: A state-of-the-art review of burn-in decisions. Proceedings of the IEEE, 1983, 71, 1257-1266. | 21.3 | 126 |
| 2 | Reactive Ion Etching of Sputter Deposited Tantalum Oxide and Its Etch Selectivity to Tantalum. Journal of the Electrochemical Society, 1992, 139, 579-583. | 2.9 | 60 |
| 3 | Electrical and Physical Characterization of Zirconium-Doped Tantalum Oxide Thin Films. Journal of the Electrochemical Society, 2004, 151, F59. | 2.9 | 54 |
| 4 | PECVD Silicon Nitride as a Gate Dielectric for Amorphous Silicon Thin Film Transistor: Process and Device Performance. Journal of the Electrochemical Society, 1995, 142, 186-190. | 2.9 | 53 |
| 5 | Room-temperature copper etching based on a plasmaâ€“copper reaction. Applied Physics Letters, 2001, 78, 1002-1004. | 3.3 | 51 |
| 6 | Thin-Film Transistor and Ultra-Large Scale Integrated Circuit: Competition or Collaboration. Japanese Journal of Applied Physics, 2008, 47, 1845. | 1.5 | 48 |
| 7 | Hafnium-doped tantalum oxide high-k dielectrics with sub-2 nm equivalent oxide thickness. Applied Physics Letters, 2005, 87, 232906. | 3.3 | 47 |
| 8 | Electrical reliability aspects of HfO2 high-k gate dielectrics with TaN metal gate electrodes under constant voltage stress. Microelectronics Reliability, 2006, 46, 69-76. | 1.7 | 46 |
| 9 | Hafnium-Doped Tantalum Oxide High-k Gate Dielectrics. Journal of the Electrochemical Society, 2006, 153, G410. | 2.9 | 45 |
| 10 | Polycrystalline silicon formation by pulsed rapid thermal annealing of amorphous silicon. Applied Physics Letters, 1996, 69, 1092-1094. | 3.3 | 41 |
| 11 | Chlorine Plasma/Copper Reaction in a New Copper Dry Etching Process. Journal of the Electrochemical Society, 2001, 148, G524. | 2.9 | 41 |
| 12 | Zirconium-Doped Hafnium Oxide High-k Dielectrics with Subnanometer Equivalent Oxide Thickness by Reactive Sputtering. Electrochemical and Solid-State Letters, 2007, 10, H199. | 2.2 | 40 |
| 13 | Plasma Etching and Deposition for aâ€Si:H Thin Film Transistors. Journal of the Electrochemical Society, 1995, 142, 2486-2507. | 2.9 | 39 |
| 14 | Sub 2 nm Thick Zirconium Doped Hafnium Oxide High-K Gate Dielectrics. ECS Transactions, 2006, 1, 447-454. | 0.5 | 39 |
| 15 | Suppression of Crystallization of Tantalum Oxide Thin Film by Doping with Zirconium. Electrochemical and Solid-State Letters, 2005, 8, G27. | 2.2 | 37 |
| 16 | Memory functions of nanocrystalline cadmium selenide embedded ZrHfO high-kdielectric stack. Journal of Applied Physics, 2014, 115, 084113. | 2.5 | 37 |
| 17 | Plasma enhanced chemical vapor deposited silicon nitride as a gate dielectric film for amorphous silicon thin film transistorsâ€”a critical review. Vacuum, 1998, 51, 741-745. | 3.5 | 36 |
| 18 | Reactive Ion Etching of PECVD Amorphous Silicon and Silicon Nitride Thin Films with Fluorocarbon Gases. Journal of the Electrochemical Society, 1990, 137, 1235-1239. | 2.9 | 35 |

| # | Article | IF | Citations |
|---|---|---|---|
| 19 | Etch mechanism in the low refractive index silicon nitride plasmaâ€enhanced chemical vapor deposition process. Applied Physics Letters, 1993, 63, 144-146. | 3.3 | 35 |
| 20 | A Novel Plasma-Based Copper Dry Etching Method. Japanese Journal of Applied Physics, 2000, 39, L188-L190. | 1.5 | 33 |
| 21 | Acetic Acid Extraction by Solvent Membrane. Separation Science and Technology, 1983, 18, 421-440. | 2.5 | 32 |
| 22 | Nanocrystalline ruthenium oxide embedded zirconium-doped hafnium oxide high-k nonvolatile memories. Journal of Applied Physics, 2011, 110, 024101. | 2.5 | 31 |
| 23 | A light emitting device made from thin zirconium-doped hafnium oxide high-k dielectric film with or without an embedded nanocrystal layer. Applied Physics Letters, 2013, 102, . | 3.3 | 29 |
| 24 | Nonvolatile hydrogenated-amorphous-silicon thin-film-transistor memory devices. Applied Physics Letters, 2006, 89, 173503. | 3.3 | 28 |
| 25 | Reactive ion etch damages in inverted, trilayer thinâ€film transistor. Applied Physics Letters, 1992, 61, 2790-2792. | 3.3 | 27 |
| 26 | Hydrogen bromide plasmaâ€“copper reaction in a new copper etching process. Thin Solid Films, 2004, 457, 326-332. | 1.8 | 27 |
| 27 | Bayesian Analysis of Hazard Rate, Change Point, and Cost-Optimal Burn-In Time for Electronic Devices. IEEE Transactions on Reliability, 2010, 59, 132-138. | 4.6 | 27 |
| 28 | Nanocrystalline Silicon Embedded Zirconium-Doped Hafnium Oxide High-kMemory Device. Japanese Journal of Applied Physics, 2006, 45, L901-L903. | 1.5 | 24 |
| 29 | Breakdown phenomena of zirconium-doped hafnium oxide high-k stack with an inserted interface layer. Applied Physics Letters, 2006, 89, 072901. | 3.3 | 24 |
| 30 | Micro light emitting device prepared from sputter deposited thin hafnium oxide film. Solid-State Electronics, 2013, 89, 120-123. | 1.4 | 23 |
| 31 | Characterization of Indium Tin Oxide and Reactive Ion Etched Indium Tin Oxide Surfaces. Japanese Journal of Applied Physics, 1990, 29, 2243-2246. | 1.5 | 20 |
| 32 | Nonvolatile Memories with Dual-Layer Nanocrystalline ZnO Embedded Zr-Doped HfO[sub 2] High-k Dielectric. Electrochemical and Solid-State Letters, 2010, 13, H83. | 2.2 | 20 |
| 33 | Light emission from conductive paths in nanocrystalline CdSe embedded Zr-doped HfO2 high-k stack. Applied Physics Letters, 2015, 106, . | 3.3 | 20 |
| 34 | Use of Adsorbents for Recovery of Acetic Acid from Aqueous Solutions Part Iâ€”Factors Governing Capacity. Separation and Purification Reviews, 1987, 16, 31-64. | 0.8 | 19 |
| 35 | A Selfâ€aligned, Trilayer, aâ€Si:H Thin Film Transistor Prepared from Two Photomasks. Journal of the Electrochemical Society, 1992, 139, 1199-1204. | 2.9 | 19 |
| 36 | Thin Film Transistors with Graded SiN x Gate Dielectrics. Journal of the Electrochemical Society, 1994, 141, 1061-1065. | 2.9 | 18 |

| # | Article | IF | Citations |
|---|---|---|---|
| 37 | A new, room-temperature, high-rate plasma-based copper etch process. Vacuum, 2004, 74, 473-477. | 3.5 | 18 |
| 38 | Reactive ion etching of plasma enhanced chemical vapor deposition amorphous silicon and silicon nitride: Feeding gas effects. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1990, 8, 1702-1705. | 2.1 | 17 |
| 39 | Reactive Ion Etching of Sputter Deposited Tantalum with CF4, CF3Cl, and CHF3. Japanese Journal of Applied Physics, 1993, 32, 179-185. | 1.5 | 17 |
| 40 | Tantalum Nitride Interface Layer Influence on Dielectric Properties of Hafnium Doped Tantalum Oxide High Dielectric Constant Thin Films. Japanese Journal of Applied Physics, 2003, 42, L769-L771. | 1.5 | 17 |
| 41 | Physical and electrical properties of Taâ€“N, Moâ€“N, and Wâ€“N electrodes on HfO[sub 2] high-k gate dielectric. Journal of Vacuum Science & Technology B, 2006, 24, 349. | 1.3 | 17 |
| 42 | Mixed Oxide High-k Gate Dielectrics - Interface Layer Structure, Breakdown Mechanism, and Memories. ECS Transactions, 2006, 3, 253-263. | 0.5 | 17 |
| 43 | Nonvolatile memory devices with AlOx embedded Zr-doped HfO2 high-k gate dielectric stack. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, 03D116. | 1.2 | 17 |
| 44 | Factors Affecting the Molybdenum Line Slope by Reactive Ion Etching. Journal of the Electrochemical Society, 1990, 137, 1907-1911. | 2.9 | 16 |
| 45 | Plasma-enhanced chemical vapor deposition of silicon nitride below 250Â°C. Vacuum, 2002, 66, 299-303. | 3.5 | 16 |
| 46 | A New Hydrogen Chloride Plasma-Based Copper Etching Process. Japanese Journal of Applied Physics, 2002, 41, 7345-7352. | 1.5 | 15 |
| 47 | Zirconium-Doped Tantalum Oxide Gate Dielectric Films Integrated with Molybdenum, Molybdenum Nitride, and Tungsten Nitride Gate Electrodes. Journal of the Electrochemical Society, 2005, 152, G643. | 2.9 | 15 |
| 48 | Charge trapping and dielectric relaxation in connection with breakdown of high-k gate dielectric stacks. Applied Physics Letters, 2006, 88, 202904. | 3.3 | 15 |
| 49 | Temperature Effects on Nanocrystalline Molybdenum Oxide Embedded ZrHfO High-kNonvolatile Memory Functions. ECS Journal of Solid State Science and Technology, 2013, 2, Q16-Q22. | 1.8 | 15 |
| 50 | Factors Affecting Light Emission from Solid State Incandescent Light Emitting Devices with Sputter Deposited Zr-Doped HfO<sub>2</sub>Thin Films. ECS Journal of Solid State Science and Technology, 2014, 3, Q182-Q189. | 1.8 | 15 |
| 51 | Nanocrystalline Zinc-Oxide-Embedded Zirconium-Doped Hafnium Oxide for Nonvolatile Memories. Journal of the Electrochemical Society, 2008, 155, H386. | 2.9 | 14 |
| 52 | Memory Functions of Nanocrystalline Indium Tin Oxide Embedded Zirconium-Doped Hafnium Oxide MOS Capacitors. Journal of the Electrochemical Society, 2007, 154, H887. | 2.9 | 13 |
| 53 | Ruthenium Modified Zr-Doped HfO2 High-k Thin Films with Low Equivalent Oxide Thickness. Journal of the Electrochemical Society, 2011, 158, G162. | 2.9 | 13 |
| 54 | Slope control of molybdenum lines etched with reactive ion etching. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1990, 8, 1529-1532. | 2.1 | 12 |

| # | Article | IF | Citations |
|---|---|---|---|
| 55 | A New Process Using Two Photoâ€Masks to Prepare Trilayer Thin Film Transistors. Journal of the Electrochemical Society, 1991, 138, 637-638. | 2.9 | 12 |
| 56 | Doping gas effects on plasma enhanced chemical vapor deposition on heavily phosphorus-doped n+silicon film. Applied Physics Letters, 1997, 71, 2821-2823. | 3.3 | 12 |
| 57 | Single- and Dual-Layer Nanocrystalline Indium Tin Oxide Embedded ZrHfO High-k Films for Nonvolatile Memories â€“ Material and Electrical Properties. Journal of the Electrochemical Society, 2011, 158, H756. | 2.9 | 12 |
| 58 | Bayesian Analysis for Accelerated Life Tests Using a Dirichlet Process Weibull Mixture Model. IEEE Transactions on Reliability, 2014, 63, 58-67. | 4.6 | 12 |
| 59 | Thinâ€film transistors with multistep deposited amorphous silicon layers. Applied Physics Letters, 1995, 67, 2173-2175. | 3.3 | 11 |
| 60 | Additive-Gas Effects on Cl[sub 2] Plasma-Based Copper-Etch Process and Sidewall Attack. Journal of the Electrochemical Society, 2008, 155, H97. | 2.9 | 11 |
| 61 | Charge detrapping and dielectric breakdown of nanocrystalline zinc oxide embedded zirconium-doped hafnium oxide high-k dielectrics for nonvolatile memories. Applied Physics Letters, 2010, 96, 192106. | 3.3 | 11 |
| 62 | White light emission from ultrathin tungsten metal oxide film. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2014, 32, . | 1.2 | 11 |
| 63 | Mechanism of a-IGZO TFT device deteriorationâ€”illumination light wavelength and substrate temperature effects. Journal Physics D: Applied Physics, 2017, 50, 42LT02. | 2.8 | 11 |
| 64 | Thin Film Technologies In Active Matrix Addressing System Of LCDs. Proceedings of SPIE, 1989, , . | 0.8 | 10 |
| 65 | Reactive ion etching of indium tin oxide by SiCl4-based plasmasâ€”substrate temperature effect. Vacuum, 1998, 51, 777-779. | 3.5 | 10 |
| 66 | Temperature Influence on Nanocrystals Embedded High-k Nonvolatile Câ€“V Characteristics. Electrochemical and Solid-State Letters, 2011, 14, H50. | 2.2 | 10 |
| 67 | Improvement of zirconium-doped hafnium oxide high-k dielectric properties by adding molybdenum. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, . | 1.2 | 10 |
| 68 | Large Area Plasma Enhanced Chemical Vapor Deposition of Nonstoichiometric Silicon Nitride. Materials Research Society Symposia Proceedings, 1992, 282, 623. | 0.1 | 9 |
| 69 | Dielectric Breakdown and Charge Trapping of Ultrathin ZrHfO/SiON High-kGate Stacks. Japanese Journal of Applied Physics, 2008, 47, 1639-1641. | 1.5 | 9 |
| 70 | Charge Trapping and Detrapping in nc-RuO Embedded ZrHfO High-k Thin Film for Nonvolatile Memory Applications. Journal of the Electrochemical Society, 2012, 159, H214-H219. | 2.9 | 9 |
| 71 | Some issues on hydrogen and hydrogenation of plasma enhanced chemical vapor deposited films in a-Si:H thin-film transistors. Vacuum, 2000, 59, 484-491. | 3.5 | 8 |
| 72 | Effects of the TaNx interface layer on doped tantalum oxide high-k films. Vacuum, 2004, 74, 539-547. | 3.5 | 8 |

| # | Article | IF | Citations |
|---|---|---|---|
| 73 | Electromigration of Flat and Bent Copper Lines Patterned with a Plasma-Based Etch Process. Journal of the Electrochemical Society, 2009, 156, H579. | 2.9 | 8 |
| 74 | Influence of a 5â€‚ÀŠ Tantalum Nitride Interface Layer on Dielectric Properties of Zirconium-Doped Tantalum Oxide High-k Films. Journal of the Electrochemical Society, 2005, 152, G617. | 2.9 | 7 |
| 75 | Reactive Ion Etching of Titanium Tungsten Thin Films. Journal of the Electrochemical Society, 2007, 154, H653. | 2.9 | 7 |
| 76 | Grain-Size Effect on a Plasma-Based Copper Etch Process. Journal of the Electrochemical Society, 2008, 155, H432. | 2.9 | 7 |
| 77 | Temperature Effect on Dielectric Breakdown and Charges Retention of Nanocrystalline Cadmium Selenide Embedded Zr-Doped HfO2 High- ${k}$ Dielectric Thin Film. IEEE Transactions on Device and Materials Reliability, 2016, 16, 561-569. | 2.0 | 7 |
| 78 | Thin-Film Transistors. , 2003, , 723-733. | | 7 |
| 79 | Use of Adsorbents for Recovery of Acetic Acid from Aqueous Solutions Part IIâ€”Factors Governing Selectivity. Separation and Purification Reviews, 1987, 16, 65-89. | 0.8 | 6 |
| 80 | Use of Adsorbents for Recovery of Acetic Acid from Aqueous Solutions Part IIIâ€”Solvent Regeneration. Separation and Purification Reviews, 1987, 16, 91-102. | 0.8 | 6 |
| 81 | Horizontally Redundant, Splitâ€Gate aâ€Si:H Thin Film Transistors. Journal of the Electrochemical Society, 1996, 143, 2680-2682. | 2.9 | 6 |
| 82 | Nonphotosensitive, Vertically Redundant Twoâ€Channel aâ€Si:H Thin Film Transistor. Journal of the Electrochemical Society, 1996, 143, 1469-1471. | 2.9 | 6 |
| 83 | Microchannel Electrophoresis Device for Separation and In Situ Detection of Proteins. Electrochemical and Solid-State Letters, 2001, 4, H23. | 2.2 | 6 |
| 84 | Embedding of Nanocrystalline Ruthenium in ZrHfO High-k Film for Nonvolatile Memories. ECS Transactions, 2008, 13, 465-470. | 0.5 | 6 |
| 85 | Surface Modification of Gel-Free Microchannel Surface Electrophoresis Device for DNA Identification. Japanese Journal of Applied Physics, 2008, 47, 2300-2305. | 1.5 | 6 |
| 86 | Charge Trapping Sites in nc-RuO Embedded ZrHfO High-k Nonvolatile Memories. Materials Research Society Symposia Proceedings, 2010, 1250, 1. | 0.1 | 6 |
| 87 | Status Review of Nanocrystals Embedded High-K Nonvolatile Memories. ECS Transactions, 2011, 35, 13-31. | 0.5 | 6 |
| 88 | Non-parametric Bayesian modeling of hazard rate with a change point for nanoelectronic devices. IIE Transactions, 2012, 44, 496-506. | 2.1 | 6 |
| 89 | Memory Functions of Molybdenum Oxide Nanodots-Embedded ZrHfO High-k. Electrochemical and Solid-State Letters, 2012, 15, H192. | 2.2 | 6 |
| 90 | Temperature Effects on Charge Storage and Transfer of Nanocrystalline CdSe Embedded Zr-Doped HfO2MOS Memory Device. ECS Journal of Solid State Science and Technology, 2016, 5, Q231-Q238. | 1.8 | 6 |

| # | Article | IF | Citations |
|---|---|---|---|
| 91 | Communicationâ€"Filtration of Light Emitted from Solid State Incandescent Light Emitting Devices. ECS Journal of Solid State Science and Technology, 2017, 6, Q39-Q41. | 1.8 | 6 |
| 92 | Numerical Analysis of Oxygen-Related Defects in Amorphous In-W-O Nanosheet Thin-Film Transistor. Nanomaterials, 2021, 11, 3070. | 4.1 | 6 |
| 93 | Singleâ€gate multichannel amorphous silicon thinâ€film transistors. Applied Physics Letters, 1995, 67, 3174-3176. | 3.3 | 5 |
| 94 | Nonvolatile Memories Based on Nanocrystalline Zinc Oxide Embedded Zirconium-doped Hafnium Oxide Thin Films. ECS Transactions, 2007, 11, 509-518. | 0.5 | 5 |
| 95 | Amorphous Silicon Based TFT and MIS Nonvolatile Memories. Materials Research Society Symposia Proceedings, 2007, 989, 3. | 0.1 | 5 |
| 96 | Influence of pin Amorphous Silicon Stack Deposition Sequence on Solar Cell Performance and Degradation. ECS Journal of Solid State Science and Technology, 2017, 6, Q29-Q33. | 1.8 | 5 |
| 97 | Failure Mechanism of Nano-Resistor Devices. ECS Transactions, 2017, 77, 79-83. | 0.5 | 5 |
| 98 | Electromigration of Plasma Etched Copper Lines of Various Widths and Lengths. ECS Transactions, 2018, 86, 41-47. | 0.5 | 5 |
| 99 | The Role of Oxygen In the CF2Cl2 Reactive Ion Etching of Pecvd Films. Materials Research Society Symposia Proceedings, 1991, 223, 249. | 0.1 | 5 |
| 100 | Factors Affecting Reactive Ion Etching Of Corning 7059 Glass. , 1989, 1037, 103. | | 4 |
| 101 | <title>New thin-film transistor structure and its processing method for liquid-crystal displays</title>. , 1991, 1456, 288. | | 4 |
| 102 | Plasma Swelling of Photoresist. Japanese Journal of Applied Physics, 1993, 32, L126-L128. | 1.5 | 4 |
| 103 | High Temperature Reactive Ion Etching of Indiumâ€Tin Oxide. Journal of the Electrochemical Society, 1997, 144, 1411-1416. | 2.9 | 4 |
| 104 | Integration of an Amorphous Silicon Thin Film Transistor with a Microchannel Electrophoresis for Protein Identification. Electrochemical and Solid-State Letters, 2006, 9, J21. | 2.2 | 4 |
| 105 | Failure Analysis of Single and Dual nc-ITO Embedded ZrHfO High-k Nonvolatile Memories. ECS Transactions, 2009, 25, 457-464. | 0.5 | 4 |
| 106 | Light Effects on Charge Trapping and Detrapping of nc-ZnO Embedded ZrHfO High-k MOS Nonvolatile Memories. ECS Transactions, 2011, 41, 93-100. | 0.5 | 4 |
| 107 | Material and Electrical Properties of Hole-Trapping Memory Capacitors Composed of nc-ITO Embedded ZrHfO High-k Films. ECS Transactions, 2011, 35, 249-255. | 0.5 | 4 |
| 108 | Nonvolatile Memory Characteristics of Nanocrystalline Molybdenum Oxide Embedded High-k Film - Device Performance and Light Wavelength Effects. Materials Research Society Symposia Proceedings, 2012, 1430, 82. | 0.1 | 4 |

| # | Article | IF | Citations |
|---|---|---|---|
| 109 | Electrical properties of nano-resistors made from the Zr-doped HfO<sub>2</sub>high-kdielectric film. Journal Physics D: Applied Physics, 2018, 51, 09LT02. | 2.8 | 4 |
| 110 | Capping Layer Effect on Lifetime of Plasma Etched Copper Lines. ECS Transactions, 2019, 89, 87-92. | 0.5 | 4 |
| 111 | Lifetime of Plasma Etched Copper Lines. ECS Transactions, 2019, 90, 65-72. | 0.5 | 4 |
| 112 | Line Width and Capping Layer Effects on Electromigration Failure of Plasma Etched Copper Lines. ECS Transactions, 2019, 92, 9-16. | 0.5 | 4 |
| 113 | a-Si:H TFT Structures. , 2004, , 183-202. | | 4 |
| 114 | Deposition of Dielectric Thin Films for a-Si:H TFT. , 2004, , 241-271. | | 4 |
| 115 | Thin Film Transistors with Layered a-Si:H Structure. Materials Research Society Symposia Proceedings, 1995, 377, 701. | 0.1 | 3 |
| 116 | Memory Functions of Amorphous Silicon-Based Floating Gate MIS Capacitors. Electrochemical and Solid-State Letters, 2007, 10, H232. | 2.2 | 3 |
| 117 | Reliability of nc-ZnO Embedded ZrHfO High-kNonvolatile Memory Devices Stressed at High Temperatures. Materials Research Society Symposia Proceedings, 2009, 1160, 1. | 0.1 | 3 |
| 118 | Poly-Si Thin Film Formation Using a Novel Low Thermal Budget Process. Materials Research Society Symposia Proceedings, 2011, 1321, 167. | 0.1 | 3 |
| 119 | Temperature Effects on Charge Transfer Mechanisms of nc-ITO Embedded ZrHfO High-kNonvolatile Memory Devices. Materials Research Society Symposia Proceedings, 2011, 1337, 123. | 0.1 | 3 |
| 120 | Electromigration study of copper lines on steps prepared by a plasma-based etch process. Journal of Applied Physics, 2012, 111, 064909. | 2.5 | 3 |
| 121 | Solid State Incandescent Light Emitting Device Made of WOx Embedded Zr-Doped HfO2 High-k Stack on Si. ECS Transactions, 2015, 66, 223-228. | 0.5 | 3 |
| 122 | A Solid-State Thin-Film Incandescent Light-Emitting Device. IEEE Transactions on Electron Devices, 2015, 62, 3536-3540. | 3.0 | 3 |
| 123 | High-performance organicâ€“inorganic hybrid optocouplers based on organic light-emitting diodes and a-Si:H photodiodes. Sensors and Actuators A: Physical, 2015, 236, 364-368. | 4.1 | 3 |
| 124 | Resistivity and Barrier Height of Nano-Resistors Made from Zr-Doped HfO 2 High- K Dielectric on Si Wafer. ECS Transactions, 2017, 77, 63-68. | 0.5 | 3 |
| 125 | Non-LCD Applications of a-Si:H TFTs. , 2004, , 485-505. | | 3 |
| 126 | Two-level differential burn-in policy for spatially heterogeneous defect units in semiconductor manufacturing. Computers and Industrial Engineering, 2021, 162, 107768. | 6.3 | 3 |

| # | Article | IF | Citations |
|---|---|---|---|
| 127 | Reactive Ion Etching Of A Multicomponent Glass Substrate. Proceedings of SPIE, 1988, , . | 0.8 | 2 |
| 128 | Nonvolatile Amorphous Silicon Thin Film Transistor Memories with the a-Si:H Embedded Gate Dielectric Structure. ECS Transactions, 2006, 3, 333-339. | 0.5 | 2 |
| 129 | Relaxation Behavior and Breakdown Mechanisms of Nanocrystals Embedded Zr-doped HfO2 High-k Thin Films for Nonvolatile Memories. Materials Research Society Symposia Proceedings, 2008, 1071, 1. | 0.1 | 2 |
| 130 | Mechanism of Charge Storage in nc-RuO Embedded ZrHfO High-k Films. ECS Transactions, 2009, 16, 309-316. | 0.5 | 2 |
| 131 | Hysteresis of Transfer Characteristics of Floating-Gate a-Si:H Thin Film Transistor Nonvolatile Memories. Electrochemical and Solid-State Letters, 2010, 13, H460. | 2.2 | 2 |
| 132 | A novel low thermal budget thin-film polysilicon fabrication process for large-area, high-throughput solar cell production. , 2010, , . | | 2 |
| 133 | Process effects of copper film over a step etched with a plasma-based process. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 021204. | 1.2 | 2 |
| 134 | Memory Functions of Nanocrystalline ITO Embedded Zirconium-Doped Hafnium Oxide High-kCapacitor with ITO Gate. Journal of the Electrochemical Society, 2012, 159, H595-H598. | 2.9 | 2 |
| 135 | Nonvolatile memories based on AlOx embedded ZrHfO high-k gate dielectric. Materials Research Society Symposia Proceedings, 2014, 1691, 37. | 0.1 | 2 |
| 136 | Light Emission Enhancement by Embedding Nanocrystalline Cadmium Selenide in Amorphous ZrHfO High-k Dielectric Thin Film Deposited on Silicon Wafer. ECS Journal of Solid State Science and Technology, 2016, 5, Q75-Q80. | 1.8 | 2 |
| 137 | Progress of Thin Film Transistor Technology. , 2018, , . | | 2 |
| 138 | Memory Functions of Cadmium Sulfide Embedded Zr-Doped HfO<sub>2</sub>High-k Dielectrics. ECS Journal of Solid State Science and Technology, 2018, 7, Q97-Q103. | 1.8 | 2 |
| 139 | Statistical Models of Overdispersed Spatial Defects for Predicting the Yield of Integrated Circuits. IEEE Transactions on Reliability, 2020, 69, 510-521. | 4.6 | 2 |
| 140 | Electromigration Study of Plasma Etched Copper Lines with Copper Oxide Capping Layers. ECS Transactions, 2020, 97, 51-60. | 0.5 | 2 |
| 141 | Geometrical Layout Effect on Light Intensity Distribution in SSI-LED. ECS Transactions, 2021, 102, 159-164. | 0.5 | 2 |
| 142 | Charge and Discharge of Floating-Gate Amorphous Silicon Thin Film Transistor Nonvolatile Memories. Journal of the Korean Physical Society, 2009, 54, 409-414. | 0.7 | 2 |
| 143 | Study of Electrothermal Characteristics and Emitted Light Characteristics of SSI-LED. ECS Journal of Solid State Science and Technology, 2020, 9, 065017. | 1.8 | 2 |
| 144 | Reactive Ion Etching Processes for Amorphous Germanium Alloys. Materials Research Society Symposia Proceedings, 1993, 316, 1041. | 0.1 | 1 |

| # | Article | IF | Citations |
|---|---|---|---|
| 145 | <title>New microchannel device for protein separation and detection</title>. , 2001, , . | | 1 |
| 146 | A new microchannel device for proteins separation and identification. , 0, , . | | 1 |
| 147 | Plasma Hydrogenation â€“ A New Method of Reducing the k Value of the Low k Polyimide Film. Materials Research Society Symposia Proceedings, 2003, 766, 8161. | 0.1 | 1 |
| 148 | Fabrication and Characterization of Hydrogenated Amorphous Silicon Bipolar Thin Film Transistor (B-TFT). Materials Research Society Symposia Proceedings, 2004, 808, 287. | 0.1 | 1 |
| 149 | Influence of Ru Dopant on the Dielectric Properties of Zr-doped HfO2 High-k Thin Film. ECS Transactions, 2007, 6, 121-127. | 0.5 | 1 |
| 150 | Failure analysis of nanocrystals embedded high-k dielectrics for nonvolatile memories. , 2008, , . | | 1 |
| 151 | Floating-Gate a-Si:H TFT Nonvolatile Memories. Materials Research Society Symposia Proceedings, 2008, 1066, 1. | 0.1 | 1 |
| 152 | Hole-Trapping Mechanism and SILC of Dual-Layer nc-ITO Embedded ZrHfO High-k Nonvolatile Memories. ECS Transactions, 2010, 28, 269-276. | 0.5 | 1 |
| 153 | Plasma Etching of Copper Thin Film over a Dielectric Step and Electromigration Failure Mechanism. Materials Research Society Symposia Proceedings, 2012, 1428, 13. | 0.1 | 1 |
| 154 | Polycrystalline Silicon Thin Film Formed By Multiple Pulsed Rapid Thermal Annealing â€“ Intrinsic a-Si Film Thickness Effect. Materials Research Society Symposia Proceedings, 2012, 1426, 269-274. | 0.1 | 1 |
| 155 | Radial Growth Model for Conical Nanobridge in Resistive Switching Memory Devices. Materials Research Society Symposia Proceedings, 2013, 1562, 1. | 0.1 | 1 |
| 156 | Introduction to the Focus Issue on Oxide Thin Film Transistors. ECS Journal of Solid State Science and Technology, 2014, 3, Y5-Y5. | 1.8 | 1 |
| 157 | P<sup>+</sup> layer effects on a-Si:H solar cell performance. , 2014, , . | | 1 |
| 158 | Post Deposition Annealing Temperature Effect on White-light Emitting of Sputter Deposited Zr-doped HfO2 Thin Film. Materials Research Society Symposia Proceedings, 2014, 1698, 65. | 0.1 | 1 |
| 159 | A solid state thin film incandescent light emitting device. , 2014, , . | | 1 |
| 160 | Narrowing of Broad Band Light Emitted from a SSI-LED. ECS Transactions, 2017, 75, 17-22. | 0.5 | 1 |
| 161 | Light Sensing of a-Si:H p-i-n DiodeMechanism of Asymmetric Charge Carrier Transfer. , 2017, 1, 1-4. | | 1 |
| 162 | Post Deposition Annealing Atmosphere Effect on Performance of Solid State Incandescent Light Emitting Device. ECS Journal of Solid State Science and Technology, 2018, 7, R3023-R3029. | 1.8 | 1 |

| # | Article | IF | Citations |
|---|---|---|---|
| 163 | Plasma-Based Copper Etch Process and Reliability. ECS Transactions, 2018, 85, 165-170. | 0.5 | 1 |
| 164 | Molybdenum Capping Layer Effect on Electromigration Failure of Plasma Etched Copper Lines. ECS Transactions, 2019, 92, 39-46. | 0.5 | 1 |
| 165 | Auxiliary structure of nano-pinnacle prepared on silicon substrate: Improving the emission intensity by 9 times in SSI-LEDs. Materials Science in Semiconductor Processing, 2019, 93, 226-230. | 4.0 | 1 |
| 166 | Communicationâ€"Co-Planar Structured Nano-Resistor Devices. ECS Journal of Solid State Science and Technology, 2019, 8, Q223-Q225. | 1.8 | 1 |
| 167 | A Differential Burn-in Policy Considering Nonhomogeneous Distribution of Spatial Defects in Semiconductor Manufacturing. , 2020, , . | | 1 |
| 168 | Self-aligned Copper Oxide Passivation Layer â€" A Study on the Reliability Effect. MRS Advances, 2020, 5, 2827-2836. | 0.9 | 1 |
| 169 | Si Wafer Dopant Concentration Effect on Light Emission of Solid State Incandescent Light Emitting Devices. ECS Journal of Solid State Science and Technology, 2020, 9, 036004. | 1.8 | 1 |
| 170 | Electrical and Optical Characteristics of WOx, ZrHfO, and Tri-Layer WOx Embedded ZrHfO High-k Based SSI-LEDs. ECS Transactions, 2021, 102, 63-69. | 0.5 | 1 |
| 171 | Plasma Etching in a-Si:H TFT Array Fabrication. , 2004, , 273-312. | | 1 |
| 172 | Deposition and Etching Mechanisms in Plasma Thin Film Processes. , 1995, , 581-593. | | 1 |
| 173 | Metal Capping Layer Effects on Electromigration Failure Phenomena of Plasma Etched Copper Lines. ECS Journal of Solid State Science and Technology, 2020, 9, 104009. | 1.8 | 1 |
| 174 | Copper Oxide Passivation Effect on Electromigration Lifetime of Plasma Etched Copper Lines. ECS Transactions, 2020, 98, 99-105. | 0.5 | 1 |
| 175 | Simulation of SSI-LED Light Emission Pattern Using Python As a Simulation Framework. ECS Meeting Abstracts, 2021, MA2021-02, 1826-1826. | 0.0 | 1 |
| 176 | Plasma oxidation as an effective method in etching copper interconnect lines at room-temperature. Japanese Journal of Applied Physics, 0, , . | 1.5 | 1 |
| 177 | Electrical and Optical Characteristics of SSI-LED Made from Capacitor Containing Tri-Layer WO<sub>x</sub> Embedded Zr-Doped HfO<sub>x</sub> Gate Dielectric. ECS Journal of Solid State Science and Technology, 2021, 10, 126001. | 1.8 | 1 |
| 178 | The p-channel a-Si:H Thin Film Transistor with Plasma Etched Copper Electrodes. Materials Research Society Symposia Proceedings, 2004, 808, 119. | 0.1 | 0 |
| 179 | Electrical and material characteristics of the sub 5 nm hafnium doped tantalum oxide high k film. , 0, , . | | 0 |
| 180 | A Novel Hole-Based Memory Device Fabricated from Nano ITO Embedded High-k Thin Films. , 2006, , . | | 0 |

| # | Article | IF | Citations |
|---|---|---|---|
| 181 | A Novel Hole-Based Memory Device Fabricated from Nano ITO Embedded High-k Thin Films. , 0, , . | | 0 |
| 182 | Bulk and Interface Material and Electrical Properties of Hafnium-Doped Tantalum Oxide High-K Films. ECS Transactions, 2006, 1, 177-183. | 0.5 | 0 |
| 183 | Control of Edge Shape, Sidewall Profile, and Sidewall Roughness of the Plasma Etched Copper. ECS Transactions, 2006, 1, 169-176. | 0.5 | 0 |
| 184 | Indium-Tin-Oxide Embedded in Zirconium-Doped Hafnium Oxide High-k Dielectric Films for Hole-Based Nonvolatile Memories. ECS Transactions, 2006, 3, 193-201. | 0.5 | 0 |
| 185 | Charge trapping of ultra-thin ZrHfO<inf>x</inf>/RuO<inf>x</inf>/ZrHfO<inf>x</inf> high-k stacks. , 2007, , . | | 0 |
| 186 | ULSIC vs. TFT - What Can They Learn from Each Other?. ECS Transactions, 2007, 8, 45-50. | 0.5 | 0 |
| 187 | Radiation Exposure Effect on Amorphous Silicon Thin Film Transistors. ECS Transactions, 2007, 8, 261-266. | 0.5 | 0 |
| 188 | ELECTRONICS AND PHOTONICS DIVISION AWARD ADDRESS: Thin Film Transistor and ULSIC Technologies - Parallel or Crossing?. ECS Transactions, 2007, 6, 121-132. | 0.5 | 0 |
| 189 | ELECTRONICS AND PHOTONICS DIVISION AWARD ADDRESS: Thin Film Transistor and ULSIC Technologies - Parallel or Crossing?. ECS Meeting Abstracts, 2007, , . | 0.0 | 0 |
| 190 | Electromigration of Cu Interconnect Lines Prepared by a Plasma-based Etch Process. Materials Research Society Symposia Proceedings, 2008, 1079, 1. | 0.1 | 0 |
| 191 | Single and Dual nc-ITO and nc-ZnO Embedded ZrHfO High-k Nonvolatile Memories. ECS Transactions, 2009, 19, 81-87. | 0.5 | 0 |
| 192 | Reliability of a-Si:H TFTs and Copper Interconnect Lines for Flexible Electronics. ECS Transactions, 2008, 16, 345-351. | 0.5 | 0 |
| 193 | A-Si:H TFT Nonvolatile Memories and Copper Interconnect for Rigid and Flexible Electronics. ECS Transactions, 2009, 22, 183-190. | 0.5 | 0 |
| 194 | Temperature Influence on Nanocrystals Embedded High-k Nonvolatile Memory Characteristics. ECS Transactions, 2009, 19, 41-47. | 0.5 | 0 |
| 195 | Influence of Embedded a-Si:H Layer Location on Floating-gate a-Si:H TFT Memory Functions. Materials Research Society Symposia Proceedings, 2010, 1245, 1. | 0.1 | 0 |
| 196 | (Invited) Nonvolatile Memories for Nano and Giga Electronics. ECS Transactions, 2011, 37, 157-166. | 0.5 | 0 |
| 197 | Light Wavelength Effects on Performance of a-Si:H PIN Photodiodes. Materials Research Society Symposia Proceedings, 2012, 1426, 199-204. | 0.1 | 0 |
| 198 | Crystallization of a-Si thin film using an ultra thin n<sup>+</sup> poly-Si seed layer for solar cell applications. , 2012, , . | | 0 |

| # | Article | IF | Citations |
|---|---|---|---|
| 199 | Emission spectra study of plasma enhanced chemical vapor deposition of intrinsic, n+, and p+ amorphous silicon thin films. Materials Research Society Symposia Proceedings, 2013, 1536, 133-138. | 0.1 | 0 |
| 200 | Exposure Light Wavelength Effects on Charge Trapping and Detrapping of nc-MoOx Embedded ZrHfO High-k Stack. Materials Research Society Symposia Proceedings, 2013, 1562, 1. | 0.1 | 0 |
| 201 | Nonvolatile memory MOS capacitors made of CdSe embedded ZrHfO high-k gate dielectric. Materials Research Society Symposia Proceedings, 2013, 1562, 1. | 0.1 | 0 |
| 202 | Principles and possible system-on-wafer applications of SSI-LEDs. , 2015, , . | | 0 |
| 203 | From the President: Globalization Starting from Science. Electrochemical Society Interface, 2018, 27, 7-7. | 0.4 | 0 |
| 204 | Comparison of simulated and measured light emission spectra from solid state incandescent light emitting devices. MRS Advances, 2020, 5, 2033-2041. | 0.9 | 0 |
| 205 | Electrical and Optical Characteristics of WOx, ZrHfO, and Tri-Layer WOx Embedded ZrHfO High-k Based SSI-LEDs. ECS Meeting Abstracts, 2021, MA2021-01, 1078-1078. | 0.0 | 0 |
| 206 | Layer Thickness Effect on Lifetime of Copper Oxide Passivated Plasma Etched Copper Line. ECS Transactions, 2021, 102, 167-175. | 0.5 | 0 |
| 207 | Geometrical Layout Effect on Light Intensity Distribution in SSI-LED. ECS Meeting Abstracts, 2021, MA2021-01, 1000-1000. | 0.0 | 0 |
| 208 | Layer Thickness Effect on Lifetime of Copper Oxide Passivated Plasma Etched Copper Line. ECS Meeting Abstracts, 2021, MA2021-01, 1005-1005. | 0.0 | 0 |
| 209 | Characteristics of Nickel Oxide Modified Zr-Doped HfO2 High-k Thin Films. ECS Transactions, 2021, 104, 63-67. | 0.5 | 0 |
| 210 | Si Substrate Effect on Characteristics of Solid State Incandescent Light Emitting Devices. ECS Transactions, 2021, 104, 47-53. | 0.5 | 0 |
| 211 | Deposition of Intrinsic and Doped Semiconductor Thin Films for a-Si:H TFT. , 2004, , 203-239. | | 0 |
| 212 | From the President: Past Performance Is No Guarantee of Future Results, but 116 Years of Continuous Success Is a Sign of a Great Future. Electrochemical Society Interface, 2018, 27, 7-7. | 0.4 | 0 |
| 213 | Characteristics of Nickel Oxide Modified Zr-Doped HfO2 High-k Thin Films. ECS Meeting Abstracts, 2021, MA2021-02, 626-626. | 0.0 | 0 |
| 214 | Si Substrate Effect on Characteristics of Solid State Incandescent Light Emitting Devices. ECS Meeting Abstracts, 2021, MA2021-02, 620-620. | 0.0 | 0 |
| 215 | Influence of Vertical and Radial Distances of Nano-Resistors in SSI-LEDs on Light Intensity Distributions. ECS Transactions, 2020, 98, 163-170. | 0.5 | 0 |
| 216 | (Invited) UV and Gate Stress Induced Defects in Amorphous Indium Gallium Zinc Oxide Thin Film Transistors and Self-Repair. ECS Transactions, 2020, 98, 39-46. | 0.5 | 0 |

| # | Article | IF | Citations |
|---|---|---|---|
| 217 | (Invited) UV and Gate Stress Induced Defects in Amorphous Indium Gallium Zinc Oxide Thin Film Transistors and Self-Repair. ECS Meeting Abstracts, 2020, MA2020-02, 1917-1917. | 0.0 | 0 |
| 218 | Influence of Vertical and Radial Distances of Nano-Resistors in SSI-LEDs on Light Intensity Distributions. ECS Meeting Abstracts, 2020, MA2020-02, 1965-1965. | 0.0 | 0 |
| 219 | Copper Oxide Passivation Effect on Electromigration Lifetime of Plasma Etched Copper Lines. ECS Meeting Abstracts, 2020, MA2020-02, 1383-1383. | 0.0 | 0 |
| 220 | Welcome Remarks - H03: Thin Film Transistors 15 (TFT 15). ECS Meeting Abstracts, 2020, MA2020-02, Open-Open. | 0.0 | 0 |
| 221 | Amorphous IGZO TFTs with Low Electrical Hysteresis By Using Two-Photomask Process. ECS Meeting Abstracts, 2020, MA2020-02, 1927-1927. | 0.0 | 0 |
| 222 | Communicationâ€"Exploration of Plasma Oxidized Copper Oxide as a Copper Passivation Layer. ECS Journal of Solid State Science and Technology, 2022, 11, 035005. | 1.8 | 0 |
| 223 | Gate dielectric material and process effects on distribution pattern of nano-resistors in solid-state incandescent light emitting devices. MRS Advances, 0, , . | 0.9 | 0 |
| 224 | Study on Lifetimes of Plasma Etched Ru Lines. ECS Transactions, 2022, 108, 23-30. | 0.5 | 0 |
| 225 | Study on Lifetimes of Plasma Etched Ru Lines. ECS Meeting Abstracts, 2022, MA2022-01, 1271-1271. | 0.0 | 0 |
| 226 | Comparison of Temperature and Light Distributions Around Nano-Resistors in SSI-LEDs. ECS Meeting Abstracts, 2022, MA2022-01, 1303-1303. | 0.0 | 0 |